

ABSTRACT

Provided is a treatment liquid for a semiconductor with ruthenium, containing a hypobromite ion. Also provided is a treatment liquid for a semiconductor with
5 ruthenium, containing at least a bromine-containing compound, an oxidizing agent, a basic compound, and water which are added and mixed, wherein the liquid has the bromine-containing compound added in an amount of 0.01 mass% or more and less than 2 mass% as a bromine element content with respect to the total mass of the liquid, has the oxidizing agent added in an amount of 0.1 mass% or more and 10
10 mass% or less with respect to the total mass, and has a pH of 8 or more and 14 or less. Further provided is a method of producing a treatment liquid for a semiconductor with ruthenium, including a step of mixing a bromine-containing compound with a solution containing a hypochlorous acid compound and a basic compound.